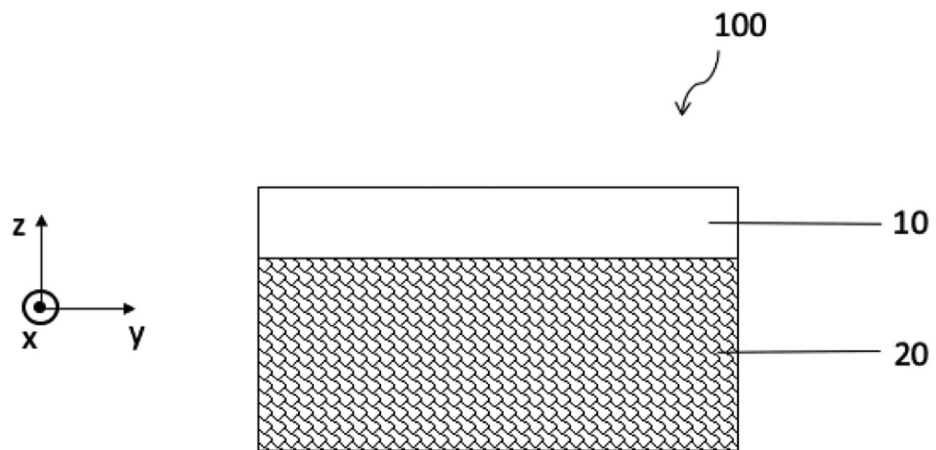


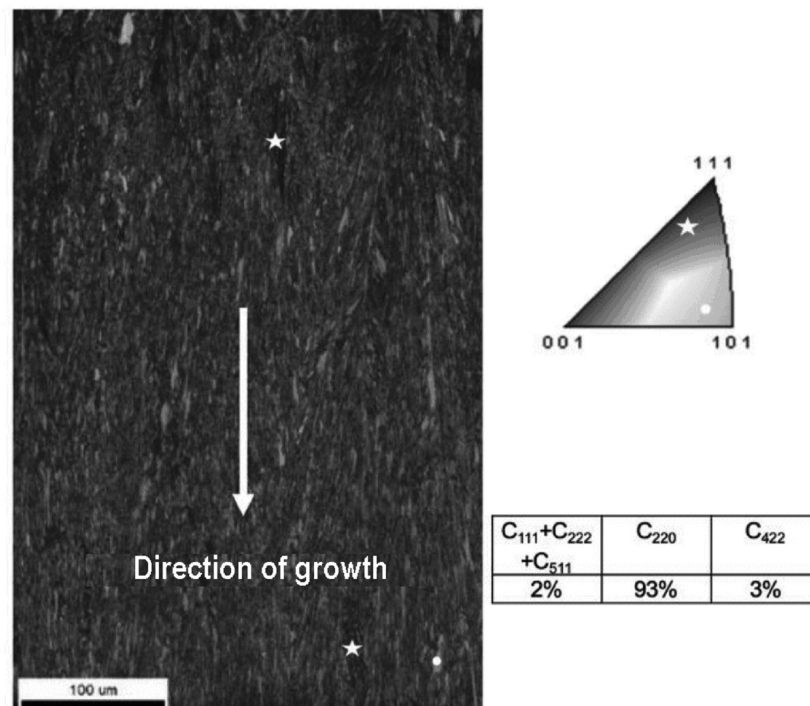
[Fig. 1]



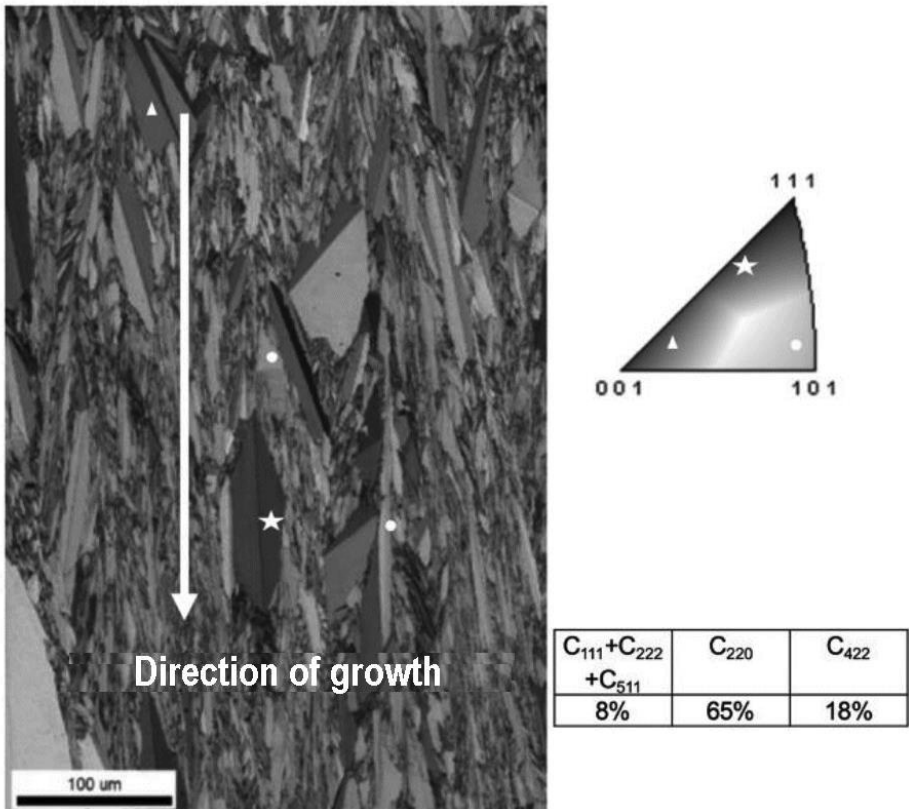
[Fig. 2]

hkl	Position 2θ of the peaks [$^{\circ}$]	Theoretical intensity I_0 [%] (Source ICDD)
111	[34.940 $^{\circ}$ - 36.345 $^{\circ}$]	100
200	[41.230 $^{\circ}$ - 41.584 $^{\circ}$]	23
220	[59.494 $^{\circ}$ - 60.452 $^{\circ}$]	57
311	[71.167 $^{\circ}$ - 72.348 $^{\circ}$]	48
222	[75.303 $^{\circ}$ - 75.749 $^{\circ}$]	10
400	[89.575 $^{\circ}$ - 90.298 $^{\circ}$]	12
331	[100.250 $^{\circ}$ - 101.537 $^{\circ}$]	25
420	[104.045 $^{\circ}$ - 104.885 $^{\circ}$]	13
422	[119.276 $^{\circ}$ - 120.418 $^{\circ}$]	14
511	[132.367 $^{\circ}$ - 134.021 $^{\circ}$]	15

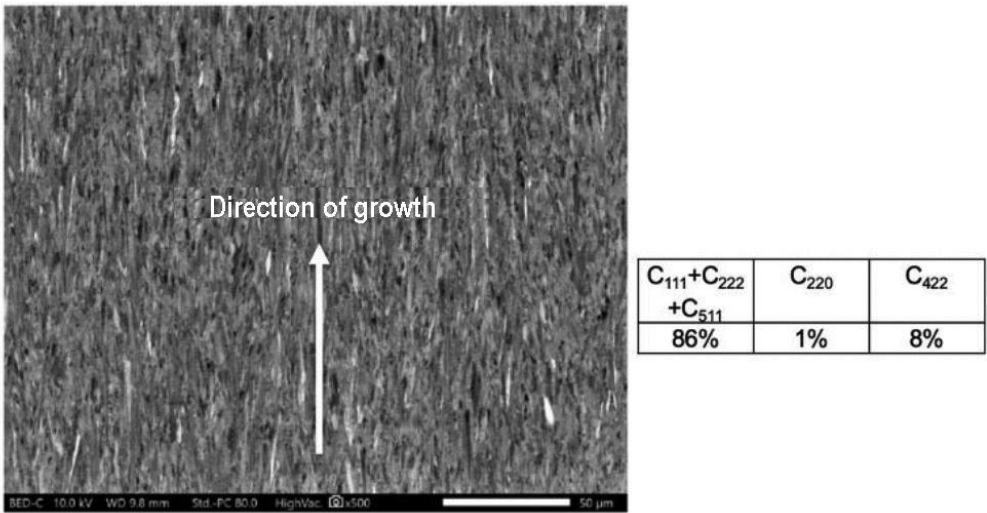
[Fig. 3a]



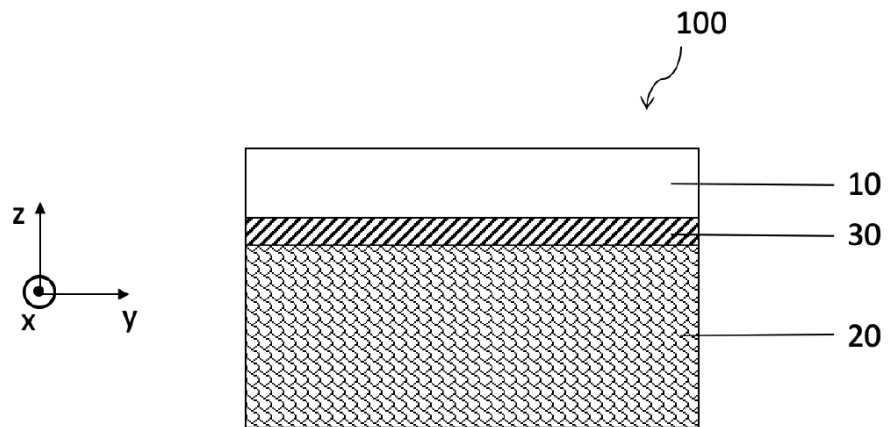
[Fig. 3b]



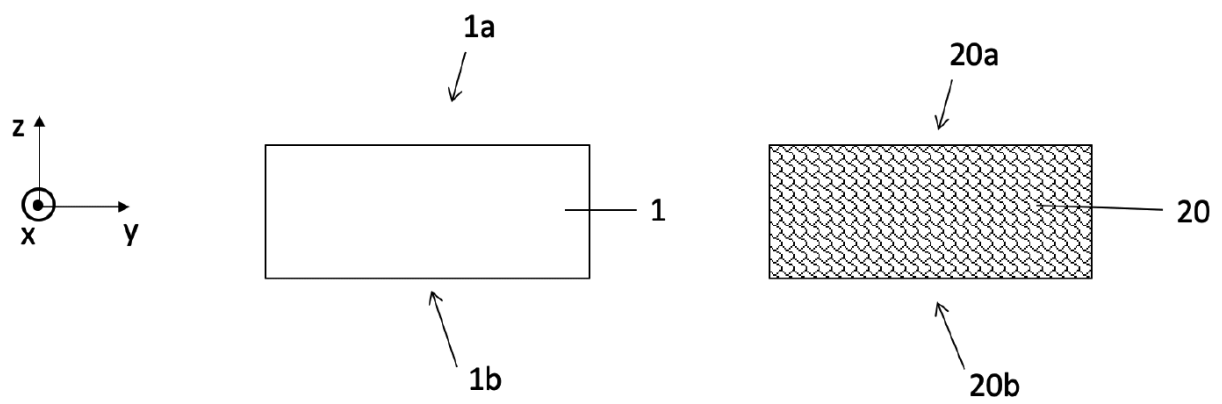
[Fig. 3c]



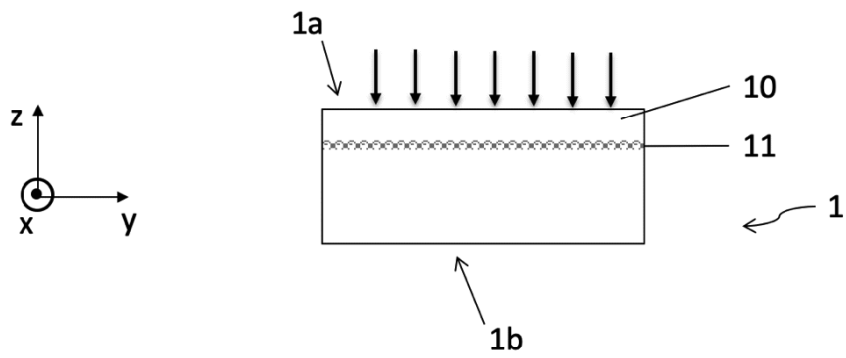
[Fig. 4]



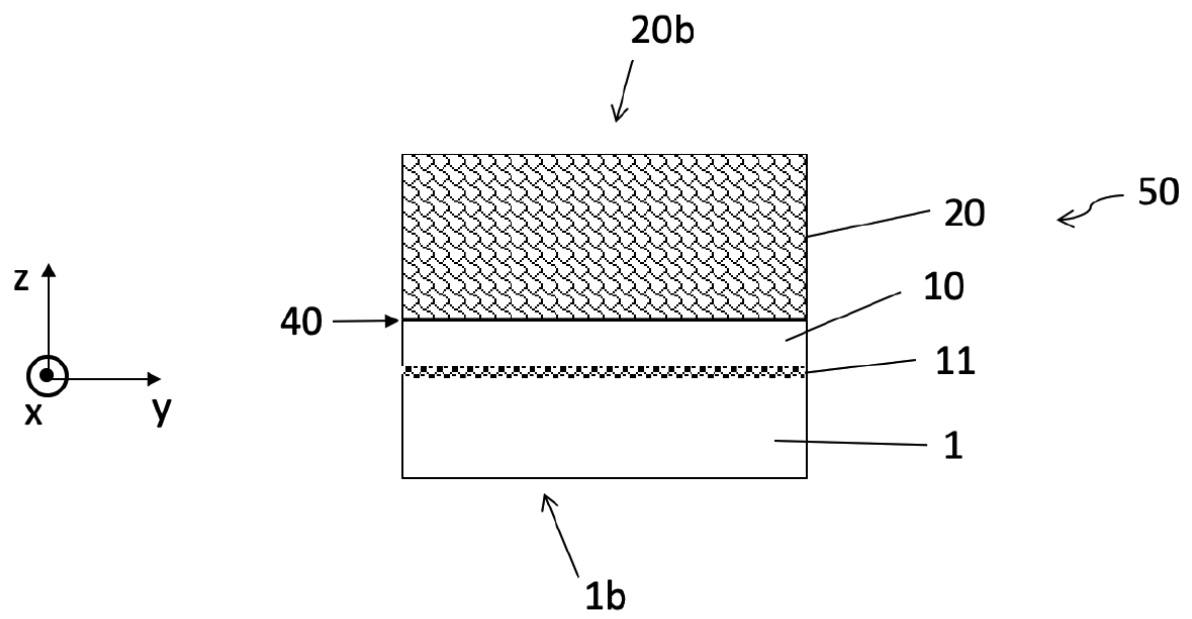
[Fig. 5a]



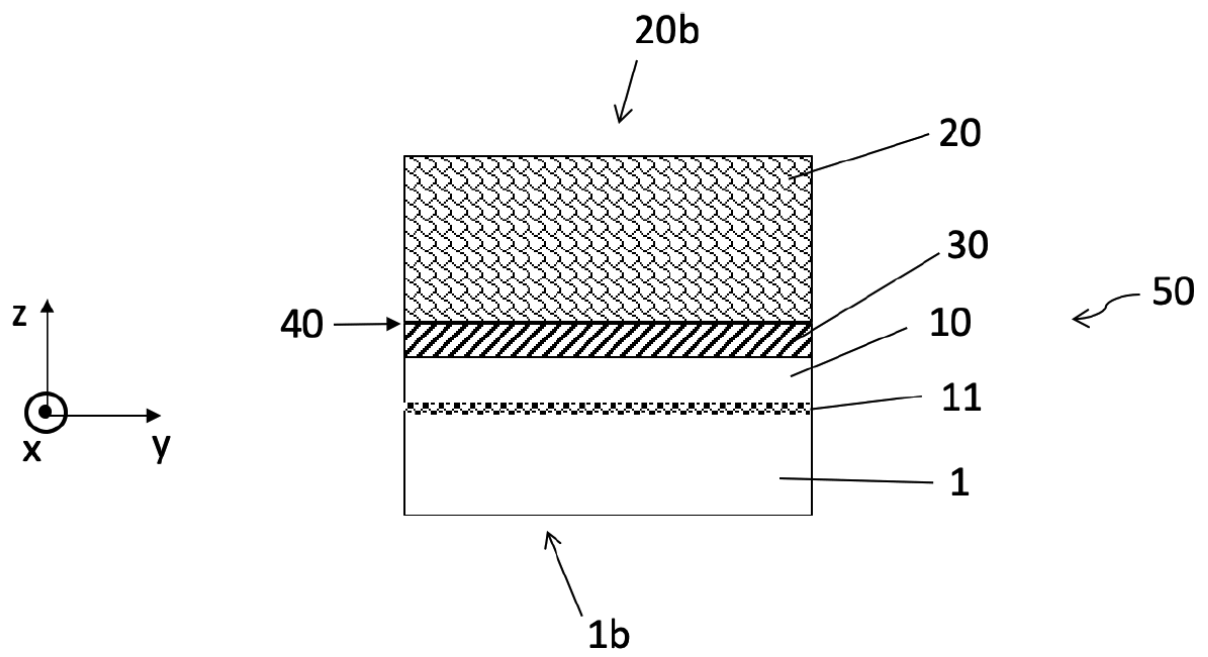
[Fig. 5b]



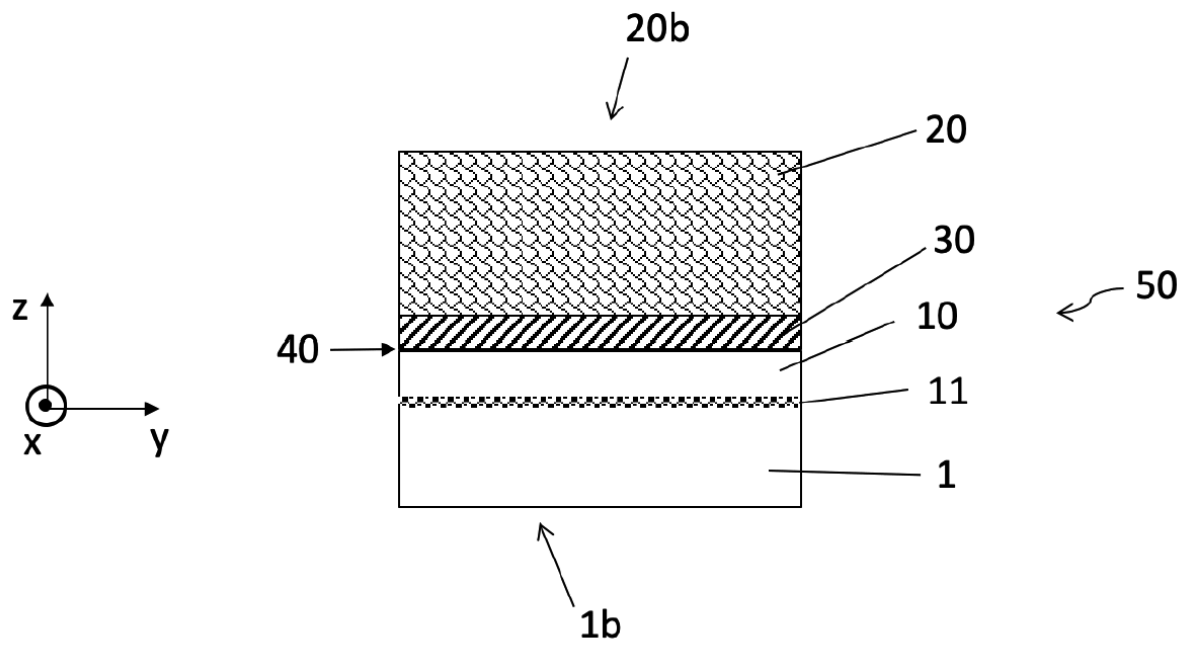
[Fig. 5c]



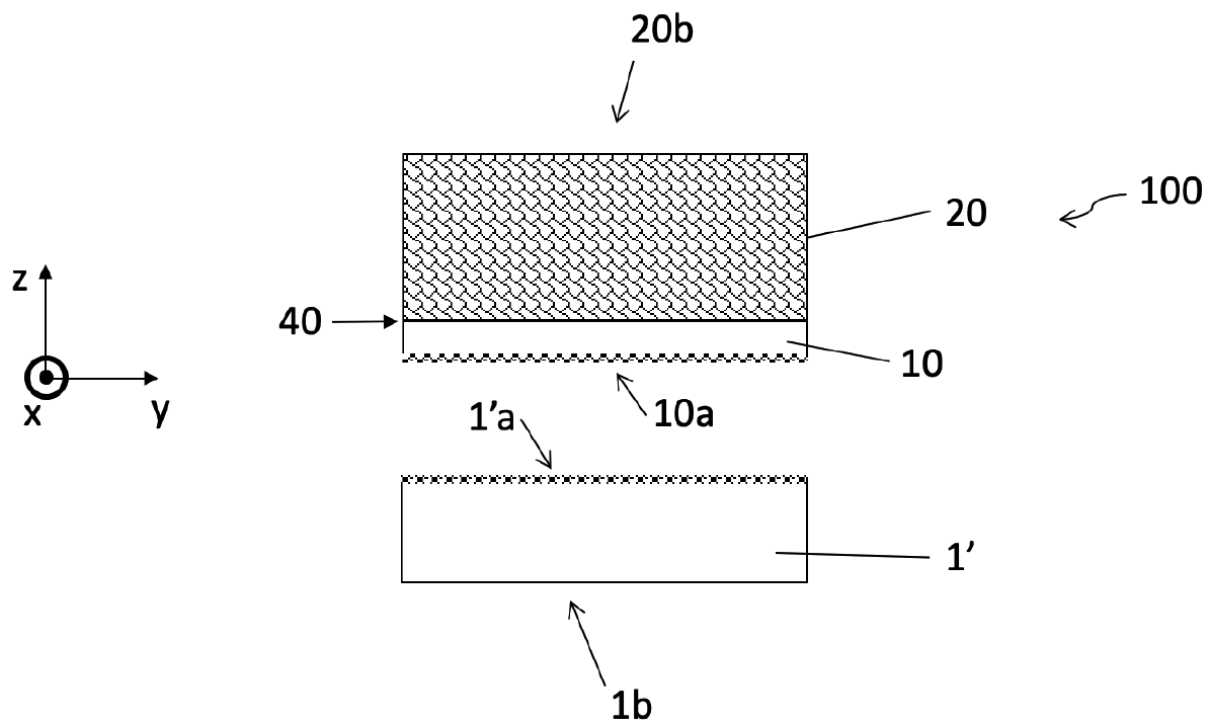
[Fig. 5c']



[Fig. 5c'']



[Fig. 5d]



[Fig. 6]

#	1	2	3	4	5
Temperature (°C)	1277	1277	1277	1327	1327
MTCS precursor gas (mbar)	23	8	16	16	16
NH3 doping gas (%)	3	6	4	4	6
% C ₂₂₀	1	1	93	65	7
% C ₁₁₁ + C ₂₂₂ +C ₅₁₁	9	86	2	8	20
% C ₄₂₂	80	8	3	18	54
N-dopant (at/cm ³)	8 x10 ¹⁹	7 x10 ²⁰	1.8 x10 ²⁰	2.2x10 ²⁰	6.8x10 ²⁰
Resistivity (mOhm.cm)	16	1.1	5	3.3	0.9
Thermal conductivity (W/m/K)	210	52	270	215	130
Raw p-SiC Wafer Thickness (um)	650	650	650	800	800
Raw p-SiC Wafer Curvature (150 mm) [um]	850	190	210	235	650
p-SiC Support Substrate (20) Curvature (150 mm) [um]	-	< 100	< 100	< 100	-